

N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
20	0.020 at V _{GS} = 4.5 V	6	10 nC
	0.025 at V _{GS} = 2.5 V	6	

FEATURES

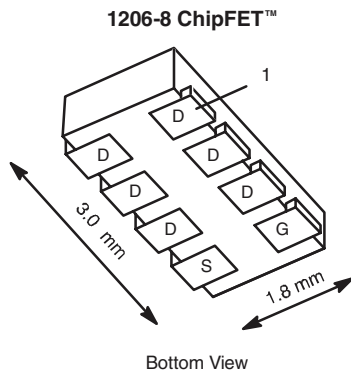
- Halogen-free
- TrenchFET[®] Power MOSFET



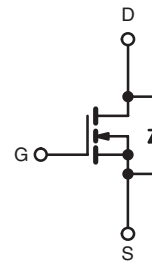
RoHS
COMPLIANT

APPLICATIONS

- Load Switches for Portable Devices



Bottom View



N-Channel MOSFET

Ordering Information: Si5432DC-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	20	V	
Gate-Source Voltage	V _{GS}	± 12	V	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	6 ^a	A	
	T _C = 70 °C	6 ^a		
	T _A = 25 °C	6 ^{a, b, c}		
	T _A = 70 °C	6 ^{a, b, c}		
Pulsed Drain Current	I _{DM}	30		
Continuous Source-Drain Diode Current	T _C = 25 °C	5.2		
	T _A = 25 °C	2.1 ^{b, c}		
Maximum Power Dissipation	T _C = 25 °C	6.3	W	
	T _C = 70 °C	4		
	T _A = 25 °C	2.5 ^{b, c}		
	T _A = 70 °C	1.6 ^{b, c}		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) ^{e, f}		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c, d}	R _{thJA}	40	50	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	15	20		

Notes:

- Package limited, T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 95 °C/W.
- See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		25		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4.0		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6		1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 8.3\text{ A}$		0.016	0.020	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 4.5\text{ A}$		0.020	0.025	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 8.3\text{ A}$		45		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1200		pF
Output Capacitance	C_{oss}			220		
Reverse Transfer Capacitance	C_{rss}			100		
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 8.3\text{ A}$		22	33	nC
				10	15	
Gate-Source Charge	Q_{gs}	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 8.3\text{ A}$		2.5		
Gate-Drain Charge	Q_{gd}			1.7		
Gate Resistance	R_g	$f = 1\text{ MHz}$		2.4		Ω
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 6.7\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		15	25	ns
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			35	55	
Fall Time	t_f			12	20	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 6.7\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		10	15	
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			25	40	
Fall Time	t_f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			5.2	A
Pulse Diode Forward Current	I_{SM}				30	
Body Diode Voltage	V_{SD}	$I_S = 6.7\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 6.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		20	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			10	20	nC
Reverse Recovery Fall Time	t_a			10		ns
Reverse Recovery Rise Time	t_b			10		

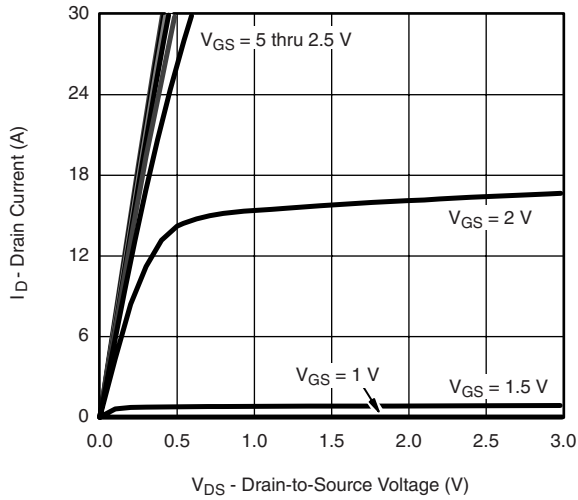
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing.

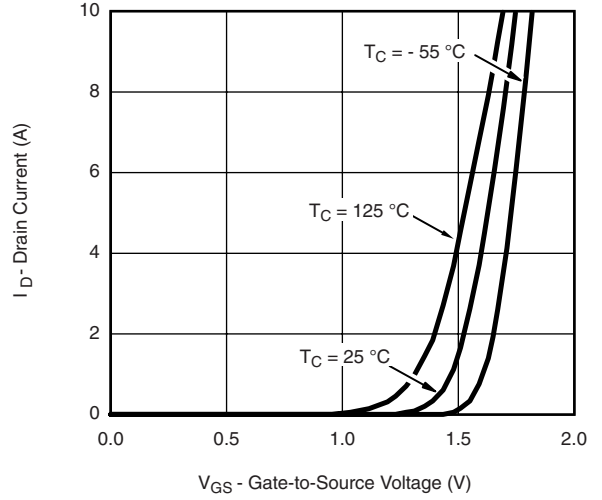
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



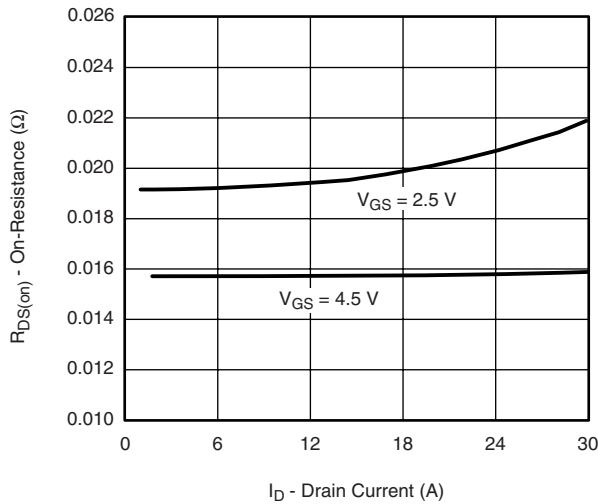
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



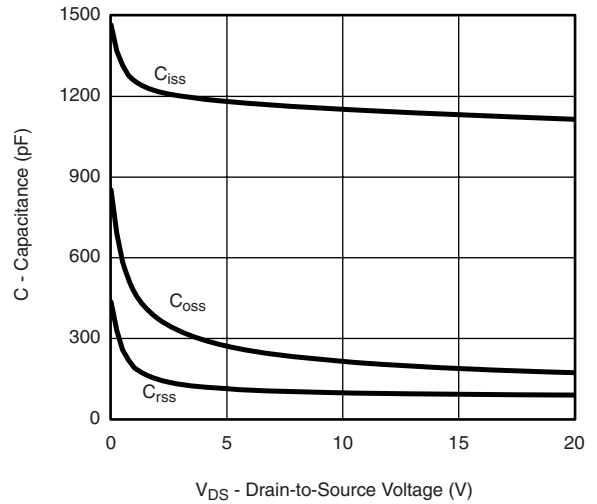
V_{DS} - Drain-to-Source Voltage (V)
Output Characteristics



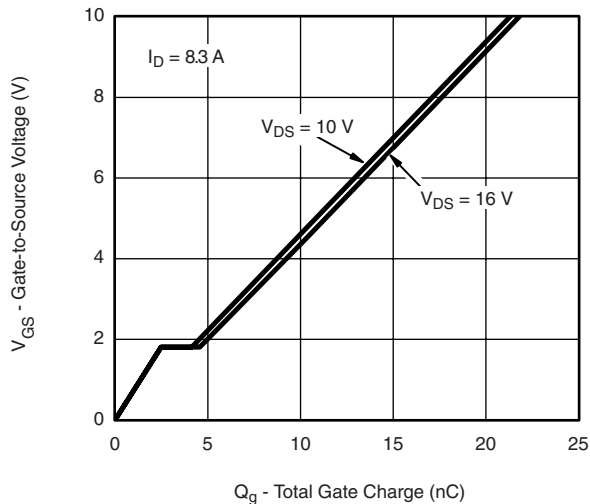
V_{GS} - Gate-to-Source Voltage (V)
Transfer Characteristics



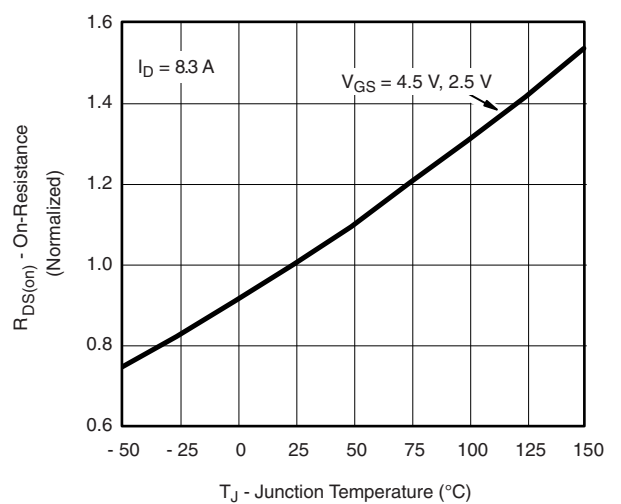
I_D - Drain Current (A)
On-Resistance vs. Drain Current



V_{DS} - Drain-to-Source Voltage (V)
Capacitance



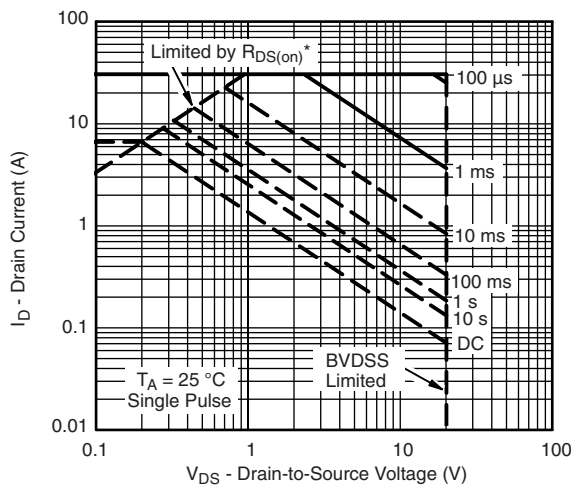
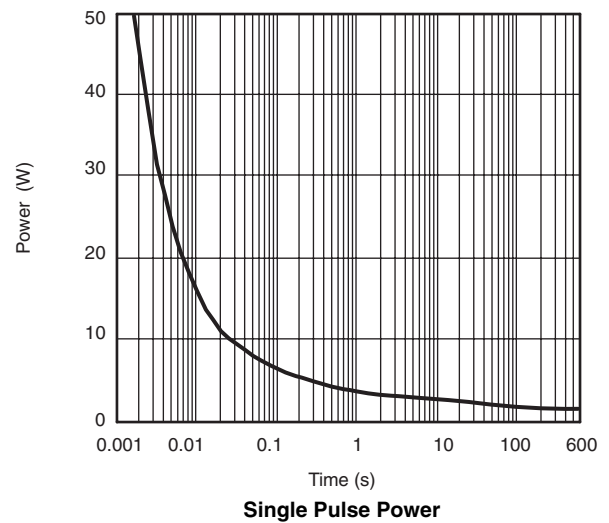
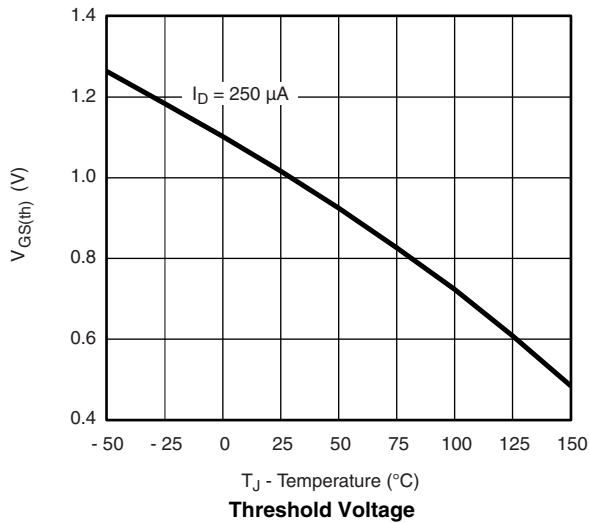
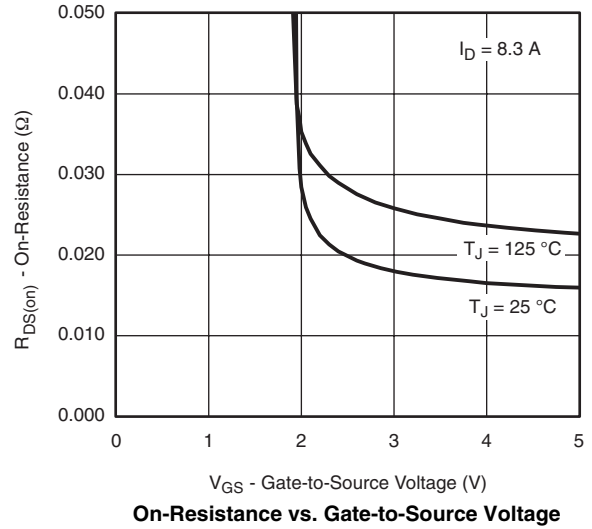
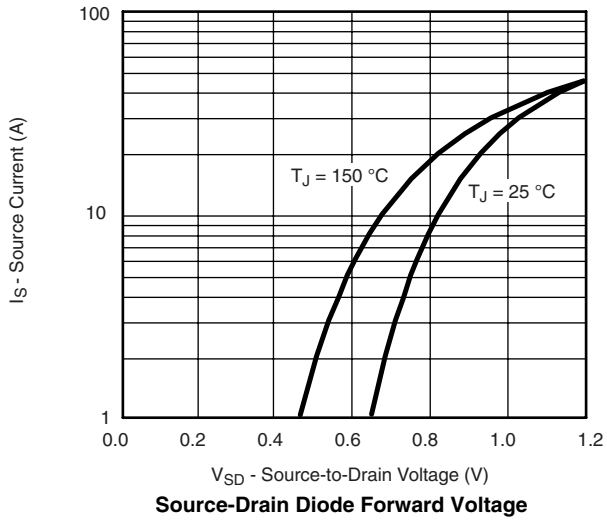
Q_g - Total Gate Charge (nC)
Gate Charge



T_J - Junction Temperature ($^\circ\text{C}$)
On-Resistance vs. Junction Temperature



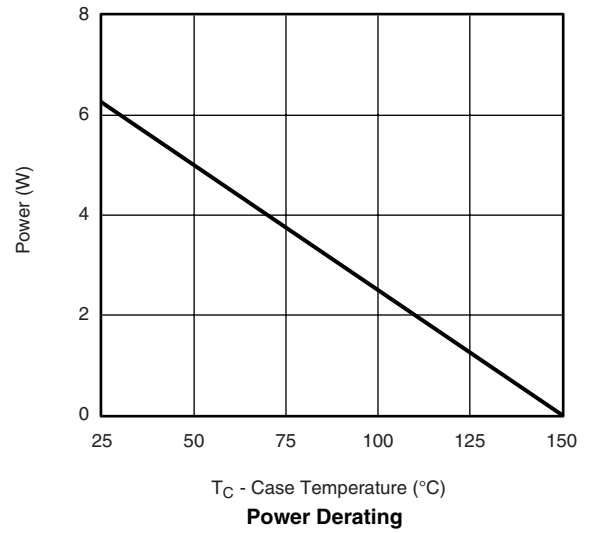
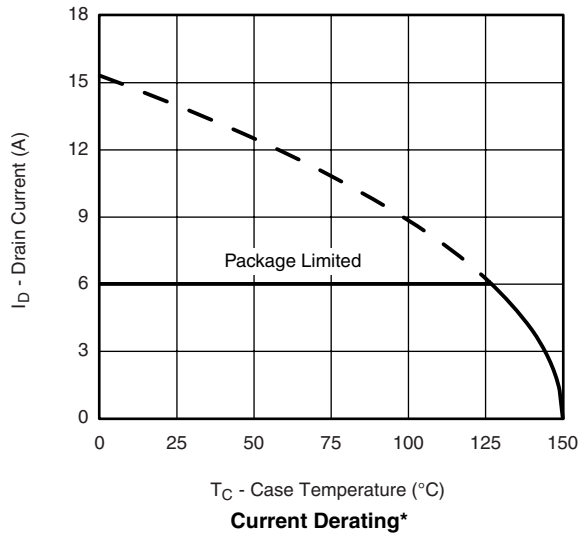
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



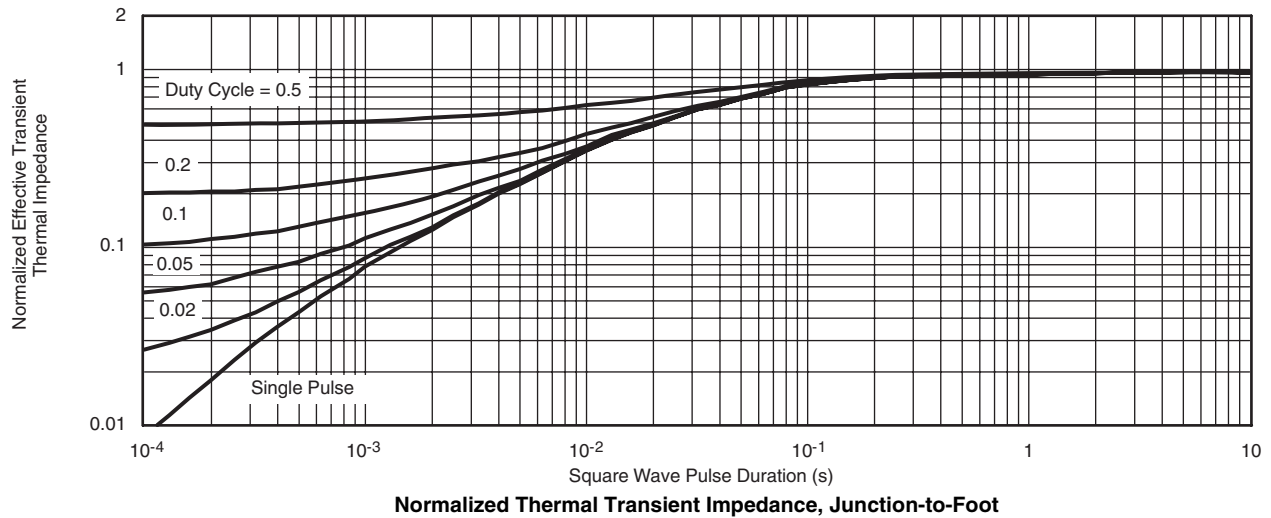
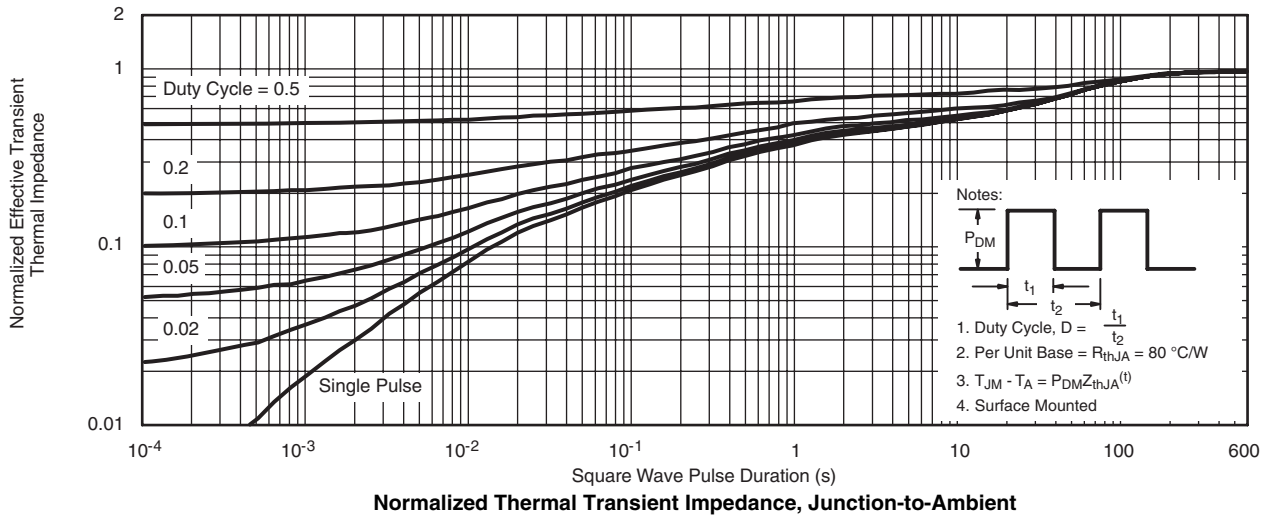
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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